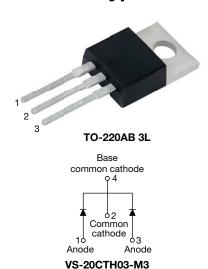


www.vishay.com

Vishay Semiconductors

Hyperfast Rectifier, 2 x 10 A FRED Pt®



PRIMARY CHARACTERISTICS									
$I_{F(AV)}$	2 x 10 A								
V_{R}	300 V								
V _F at I _F	0.85 V								
t _{rr} typ.	See Recovery table								
T_J max.	175 °C								
Package	TO-220AB 3L								
Circuit configuration	Common cathode								

FEATURES

- Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current



HALOGEN

- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

300 V series are the state of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diodes in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Peak repetitive reverse voltage	V_{RRM}		300	V						
Average restified forward current per diode		T _C = 160 °C	10							
Average rectified forward current per device	I _{F(AV)}		20	Α						
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	120							
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	300	-	-	.,				
For and allows	V _F	I _F = 10 A	1.25	V						
Forward voltage		I _F = 10 A, T _J = 125 °C	-	0.85	0.95					
Reverse leakage current		$V_R = V_R$ rated	-	-	20					
neverse leakage current	I _R	$T_J = 125$ °C, $V_R = V_R$ rated	-	6	200	μA				
Junction capacitance	C _T	V _R = 300 V	-	30	-	pF				
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH				



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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
		$I_F = 1 A, dI_F/dt = 50 A$	-	-	35					
Reverse recovery time	t _{rr}	$I_F = 1 A, dI_F/dt = 100$	-	-	30					
		T _J = 25 °C		-	31	-	ns - A			
		T _J = 125 °C	I _F = 10 A	-	42	-				
Dook receivery current	I _{RRM}	T _J = 25 °C		-	2.4	-				
Peak recovery current		T _J = 125 °C	$dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	5.6	-				
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	36	-	nC			
		T _J = 125 °C		-	120	-	IIC			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER SYMBOL TEST CONDITIONS MIN. TYP. MAX. UNITS										
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction-to-case per diode	R _{thJC}	Mounting surface, flat, smooth, and greased	-	-	1.5	°C/W				
Marking device		Case style TO-220AB 3L	20CTH03							

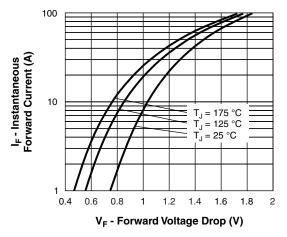


Fig. 1 - Typical Forward Voltage Drop Characteristics

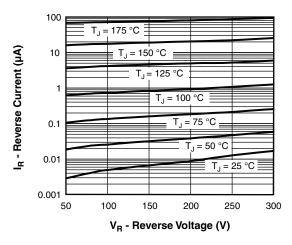


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

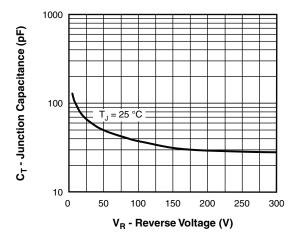


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage



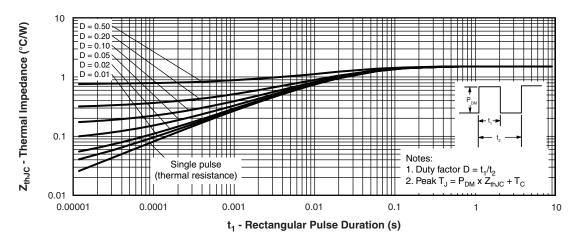


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

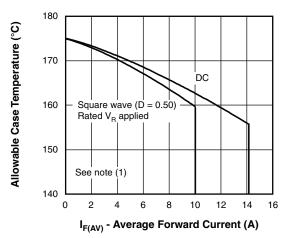


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

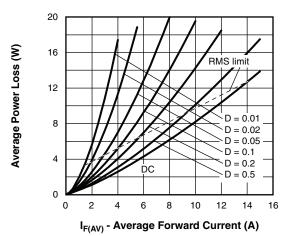


Fig. 6 - Forward Power Loss Characteristics

Note

 $^{(1)}$ Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 5); Pd_{REV} = inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = rated V_R

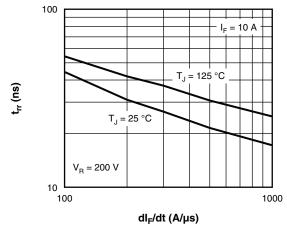


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

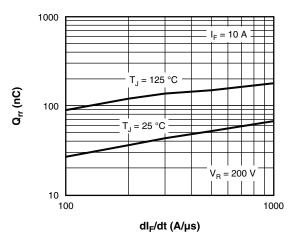
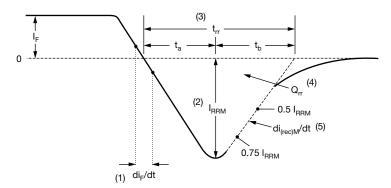


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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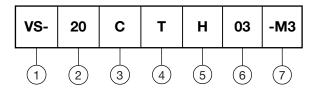


- (1) di_F/dt rate of change of current through zero crossing
- (4) Q_{rr} area under curve defined by t_{rr} and l_{RRM}
- (2) I_{RRM} peak reverse recovery current
- $Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RBM} and 0.50 I_{RBM} extrapolated to zero current.
- (5) $di_{(rec)M}/dt$ peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

Device code



- 1 Vishay Semiconductors product
- Current rating (20 = 20 A)
- **3** C = common cathode
- 4 T = TO-220, D²PAK (TO-263AB)
- **|5|** H = hyperfast recovery
- 6 Voltage rating (03 = 300 V)
- 7 Environmental digit:
 - -M3 = halogen-free, RoHS-compliant, and termination lead (Pb)-free

ORDERING INFORMATION (Example)									
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION							
VS-20CTH03-M3	50	Antistatic plastic tubes							

LINKS TO RELATED DOCUMENTS							
Dimensions <u>www.vishay.com/doc?96154</u>							
Part marking information	www.vishay.com/doc?95028						
SPICE model	www.vishay.com/doc?96583						



Vishay Semiconductors

TO-220AB 3L

DIMENSIONS in millimeters and inches





Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIM	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	NOTES	STIVIBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183			D2	11.68	13.30	0.460	0.524	6, 7
A1	1.14	1.40	0.045	0.055			Е	10.11	10.51	0.398	0.414	3, 6
A2	2.50	2.92	0.098	0.115			E1	6.86	8.89	0.270	0.350	6
b	0.69	1.01	0.027	0.040			е	2.41	2.67	0.095	0.105	
b1	0.38	0.97	0.015	0.038	4		e1	4.88	5.28	0.192	0.208	
b2	1.20	1.73	0.047	0.068			H1	6.09	6.48	0.240	0.255	6
b3	1.14	1.73	0.045	0.068	4		L	13.52	14.02	0.532	0.552	
С	0.36	0.61	0.014	0.024			L1	3.32	3.82	0.131	0.150	2
c1	0.36	0.56	0.014	0.022	4		ØΡ	3.54	3.91	0.139	0.154	
D	14.85	15.35	0.585	0.604	3		Q	2.60	3.00	0.102	0.118	
D1	8.38	9.02	0.330	0.355								

Notes

- ⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3, and c1 apply to base metal only
- Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2, and E1
- (7) Outline conforms to JEDEC® TO-220, except D2



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